TO-92 Plastic-Encapsulate Transistors

KSP12 TRANSISTOR（ NPN ）

FEATURES

Power dissipation

P_{CM}： 0.625 W（Tamb=25℃）

Collector current

I_{CM}： 1.2 A

Collector-base voltage

$V_{(BR)CBO}$： 20 V

Operating and storage junction temperature range

T_J，T_{stg}: -55℃ to +150℃

TO—92

1.EMITTER

2.BASE

3.COLLECTOR

1 2 3

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= 100μA， I_B=0	20			V
Collector cut-off current	I_{CBO}	V_{CB}= 15V , I_E=0			100	μA
Collector cut-off current	I_{CEO}	V_{CE}= 15V , I_B=0			100	μA
Emitter cut-off current	I_{EBO}	V_{EC}= 10V , I_C=0			100	μA
DC current gain(note)	H_{FE}（1）	V_{CE}=5V, I_C=10mA	20K			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=10mA, I_B=0.01 mA			1.0	V
Base-emitter voltage	V_{BE}	V_{CE}=5V, I_C=10mA			1.4	V

CLASSIFICATION OF HFE

Rank	1	2
Range	20K-30K	30K-40K